

What is claimed is:

1. An electroplating solution comprising copper ions and a complexing agent for the copper ions and having a pH in the range of 4 to 10.

5        2. An electroplating process using an electroplating solution comprising copper ions and a complexing agent for the copper ions and having a pH in the range of 4 to 10.

10       3. The electroplating process according to claim 2, wherein the plating is applied on the silicon wafer on which a conductive seed layer has been formed.

4. A silicon wafer plated with an electroplating solution comprising copper ions and a complexing agent for the copper ions and having a pH in the range of 4 to 10.

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